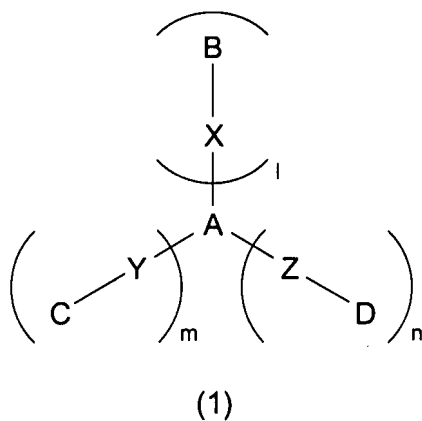
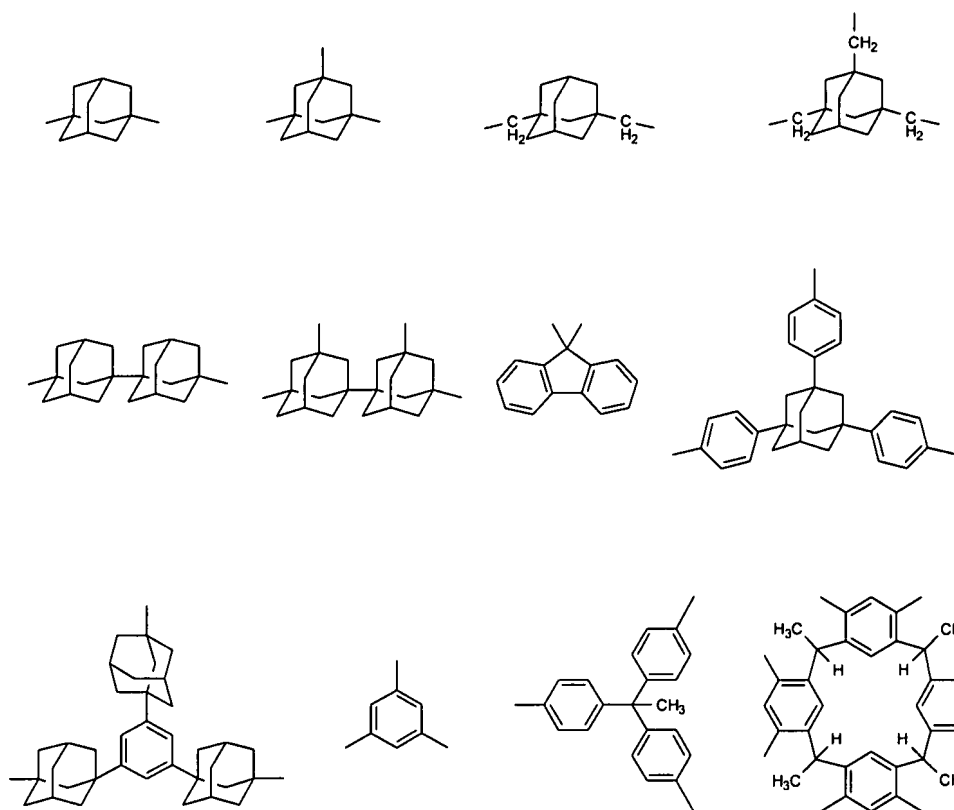


IN THE CLAIMS:

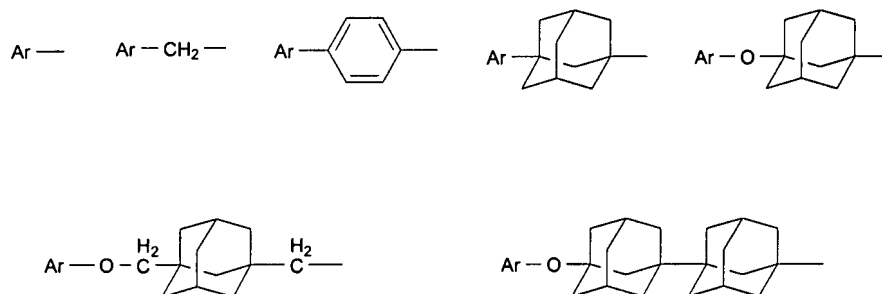
1. (Currently amended) A photoresist base material ~~comprising~~ consisting essentially of an extreme ultra-violet reactive organic compound represented by the following general formula (1),



wherein A is an organic group ~~represented by~~ selected from the group consisting
of



wherein each of B, C and D is independently an extreme ultra-violet reactive group, a group having reactivity to the action of chromophore active to extreme ultra-violet or an organic group ~~represented by~~ selected from the group consisting of



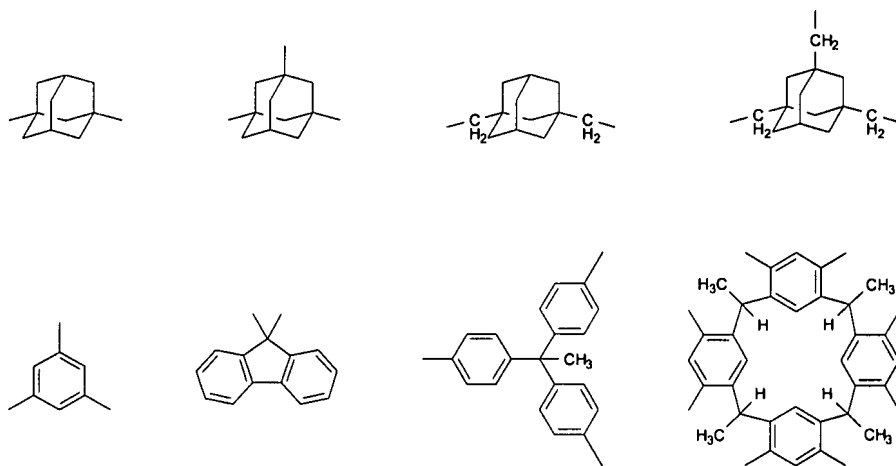
wherein Ar is a phenyl or naphthyl group substituted with RO- and/or ROCO- in which R, RO- and ROCO are extreme ultra-violet reactive groups or groups having reactivity to the action of a chromophore active to extreme ultra-violet,

wherein each of X, Y and Z is independently a single bond or an ether bond, and

$l + m + n = 2, 3, 4$ or 8.

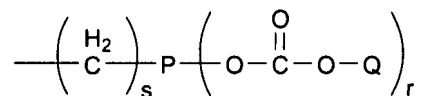
2. (Original) The photoresist base material as recited in claim 1, wherein said extreme ultra-violet reactive organic compound is in an amorphous state at room temperature and has a molecule whose average diameter is 2 nm or less.

3. (Currently amended) The photoresist base material as recited in claim 1, wherein A is an organic group ~~represented by~~ selected from the group consisting of



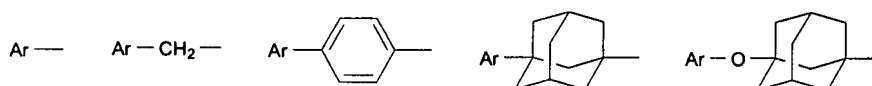
wherein each of B, C and D is selected from the group consisting of a hydrogen atom, tert-butyl, tert-butyloxycarbonylmethyl, tert-butyloxycarbonyl, 1-tetrahydropyranyl, 1-

tetrahydrofuranyl, 1-ethoxyethyl, 1-phenoxyethyl, an organic group represented by

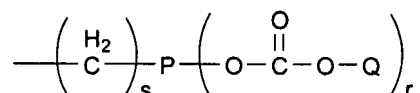


~~in which~~ wherein P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10,

~~or and~~ an organic group ~~represented by~~ selected from the group consisting of



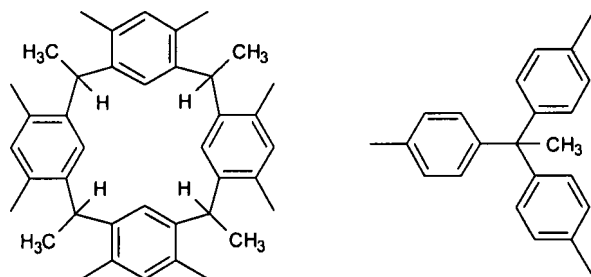
~~in which~~ wherein Ar is a phenyl or naphthyl group substituted with RO- and/or ROCO- in which R is selected from the group consisting of hydrogen, tert-butyl, tert-butyloxycarbonylmethyl, tert-butyloxycarbonyl, 1-tetrahydropyranyl, 1-tetrahydrofuranyl, 1-ethoxyethyl, 1-phenoxyethyl ~~or and~~ an organic group represented by



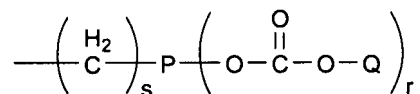
~~in which~~ wherein P is an aromatic group having a valence of (r + 1) and

having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10, and each of X, Y and Z is independently a single bond or an ether bond.

4. (Currently amended) The photoresist base material as recited in claim 3, wherein A is an organic group ~~represented by~~ selected from the group consisting of

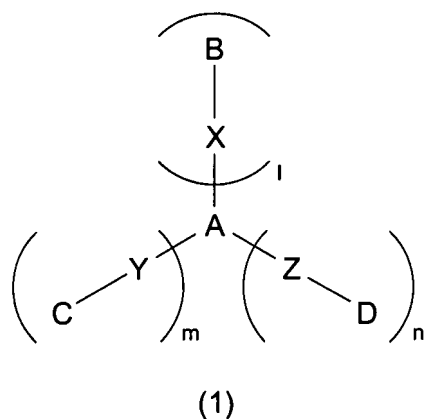


wherein each of B, C and D is selected from the group consisting of a hydrogen atom, tert-butyl, tert-butyloxycarbonylmethyl, tert-butyloxycarbonyl, 1-tetrahydropyranyl, 1-tetrahydrofuranyl, 1-ethoxyethyl, 1-phenoxyethyl ~~or~~ and an organic group represented by

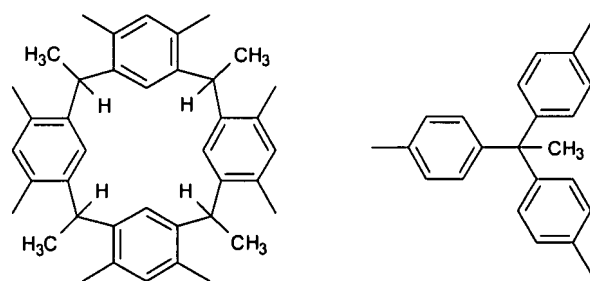


~~in which~~ wherein P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10, and X, Y and Z are ether bonds.

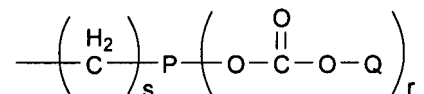
5. (Currently amended) A photoresist base material ~~comprising~~ consisting essentially of a radiation-sensitive organic compound represented by the following general formula (1),



wherein A is an organic group represented by selected from the group consisting of

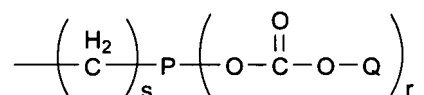


wherein each of B, C and D is independently selected from the group consisting of tert-butyloxycarbonylmethyl, tert-butyloxycarbonyl ~~or~~ and an organic group represented by



~~in which~~ wherein P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10, each of X, Y and Z is independently a single bond or an ether bond, and 1 + m + n = 3 or 8.

6. (Original) The photoresist base material as recited in claim 5, wherein the organic group represented by



is 4-(tert-butoxycarbonyloxy)benzyl or 3,5-di(tert-butoxycarbonyloxy)benzyl.

7. (Original) The photoresist base material as recited in claim 5, wherein the radiation is extreme ultra-violet or electron beam.

8. (Previously presented) The photoresist base material as recited in claim 1, wherein at least one of B, C and D is a hydrogen atom and X, Y and Z are ether bonds.
9. (Previously presented) The photoresist base material as recited in claim 1, which has a basic impurity content of 10 ppm or less.
10. (Previously presented) A photoresist composition comprising a solid content containing the photoresist base material recited in claim 1 and a solvent.
11. (Original) A photoresist composition comprising a solid content containing the photoresist base material recited in claim 9 and a solvent.
12. (Original) The photoresist composition as recited in claim 10, which further comprises an optically-acid-generating agent.
13. (Original) A method for purification of a photoresist base material, which comprises washing the photoresist base material recited in claim 1 with an acidic aqueous solution and treating the material with an ion-exchange resin.
14. (Previously presented) The method for purification of a photoresist base material as recited in claim 13, wherein said acidic aqueous solution is an acetic acid aqueous solution.

15. (Previously presented) A method for improvement of the photoresist base material recited in claim 1 in radiation sensitivity, which comprises decreasing the content of basic impurities to 10 ppm or less.

16. (Previously presented) A method for fine processing by lithography, which uses the photoresist composition recited in claim 10.

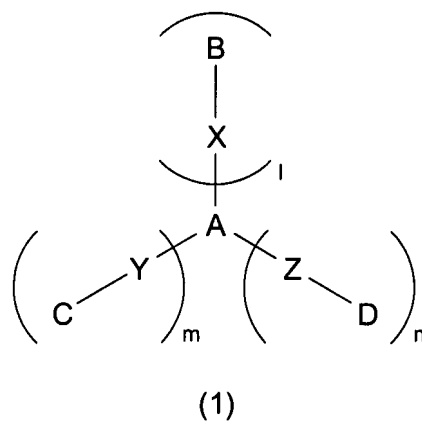
17. (Previously presented) A semiconductor device fabricated using the photoresist composition recited in claim 10.

18. (Canceled)

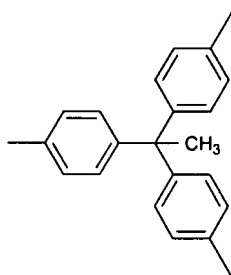
19. (Currently amended) The organic compound as recited in claim ~~18~~ 21 or 22, which has a basic impurity content of 10 ppm or less.

20. (Currently amended) A method for purification of an organic compound, which comprises washing the organic compound recited in claim ~~18~~ 21 or 22 with an acidic aqueous solution and treating the compound with an ion-exchange resin.

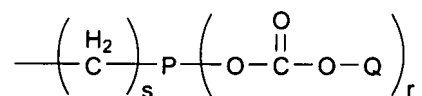
21. (New) An organic compound represented by the following general formula (1),



wherein A is an organic group represented by



wherein each of B, C and D is independently tert-butyloxycarbonylmethyl, tert-butyloxycarbonyl and an organic group represented by



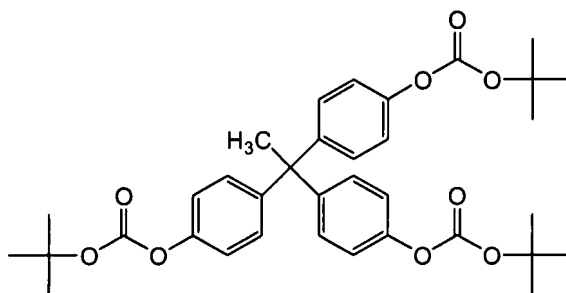
wherein P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to

10 and s is an integer of 0 to 10,

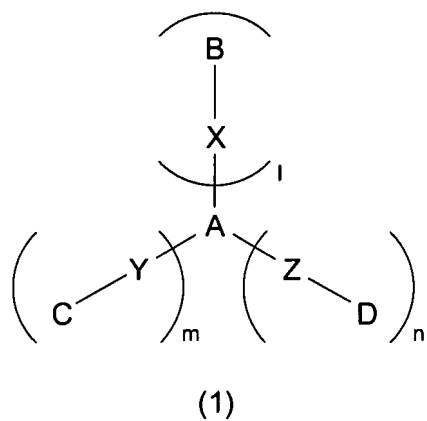
each of X, Y and Z is independently a single bond or an ether bond, and

$$l + m + n = 3;$$

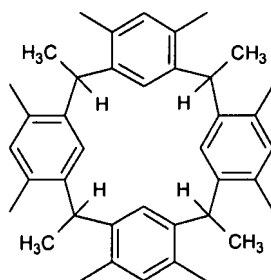
provided that excluded is the organic compound represented as follows



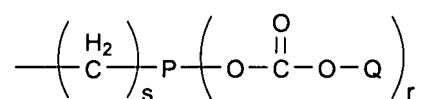
22. (New) An organic compound represented by the following general formula (1),



wherein A is an organic group represented by



wherein each of B, C and D is independently an organic group represented by

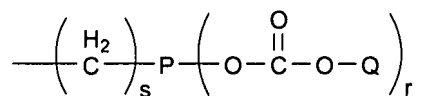


wherein P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10,

each of X, Y and Z is independently a single bond or an ether bond, and

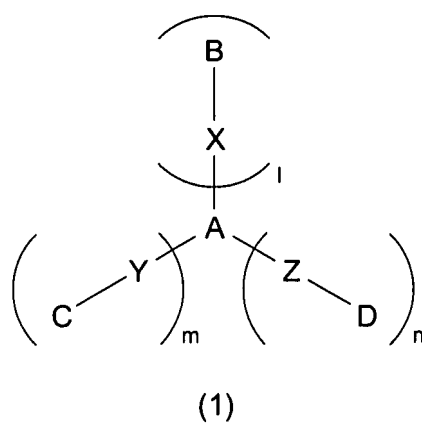
$$l + m + n = 8.$$

23. (New) The organic compound as recited in claim 21 or 22, wherein the organic group represented by

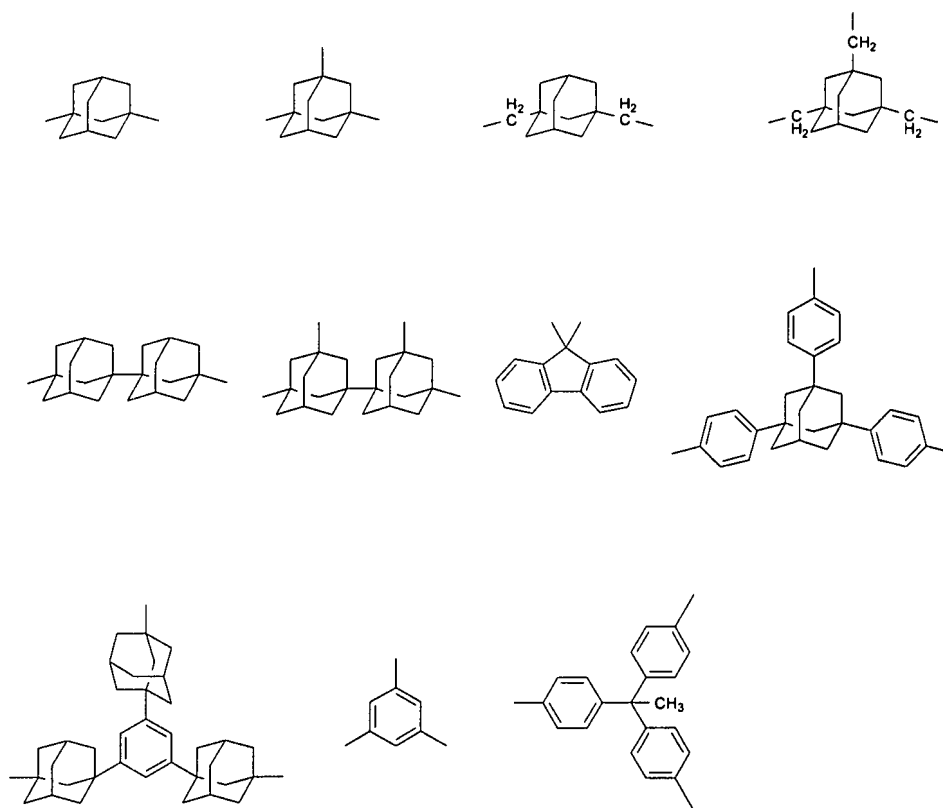


is 4-(tert-butoxycarbonyloxy)benzyl or 3,5-di(tert-butoxycarbonyloxy)benzyl.

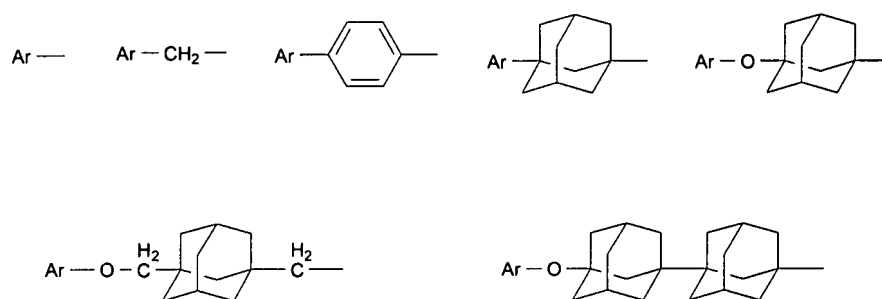
24. (New) A photoresist base material comprising an extreme ultra-violet reactive organic compound represented by the following general formula (1),



wherein A is an organic group selected from the group consisting of



wherein each of B, C and D is independently an extreme ultra-violet reactive group selected from the group consisting of



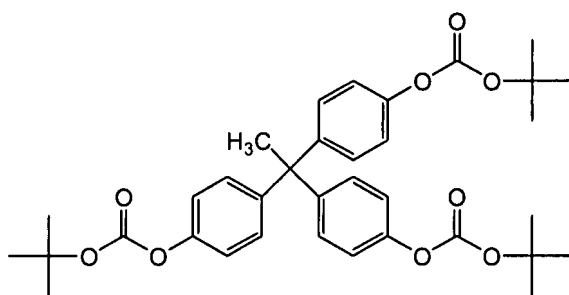
wherein Ar is a phenyl or naphthyl group substituted with RO- and/or ROCO- in

which R, RO- and ROCO are extreme ultra-violet reactive groups or groups having reactivity to the action of a chromophore active to extreme ultra-violet,

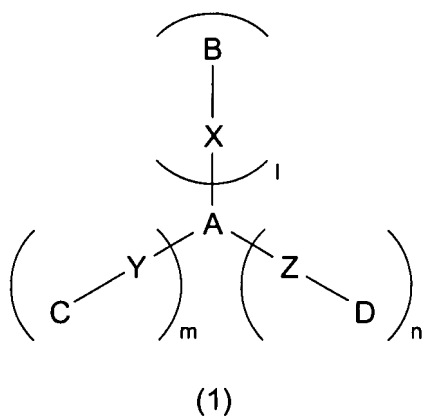
wherein each of X, Y and Z is independently a single bond or an ether bond, and

$l + m + n = 2, 3$ or 4 ;

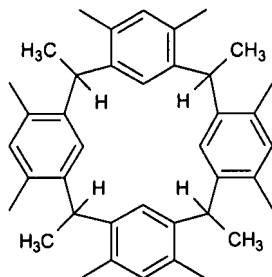
provided that excluded is the organic compound represented as follows



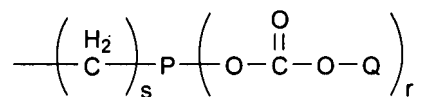
25. (New) A photoresist base material comprising an extreme ultra-violet reactive organic compound represented by the following general formula (1),



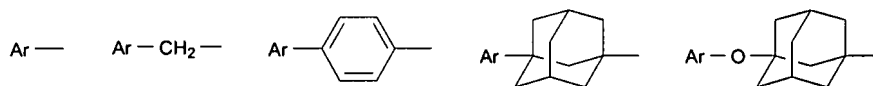
wherein A is an organic group represented by



wherein each of B, C and D is selected from the group consisting of tert-butyl, 1-tetrahydropyranyl, 1-tetrahydrofuranyl, 1-ethoxyethyl, 1-phenoxyethyl, an organic group represented by

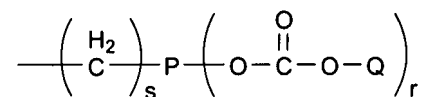


wherein P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10, and an organic group selected from the group consisting of



wherein Ar is a phenyl or naphthyl group substituted with RO- and/or ROCO- in which R is selected from the group consisting of hydrogen, tert-butyl, tert-

butyloxycarbonylmethyl, tert-butyloxycarbonyl, 1-tetrahydropyranyl, 1-tetrahydrofuranyl, 1-ethoxyethyl, 1-phenoxyethyl and an organic group represented by



wherein P is an aromatic group having a valence of (r + 1) and having 6 to 20 carbon atoms, Q is an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10 and s is an integer of 0 to 10,

and wherein each of X, Y and Z is independently a single bond or an ether bond,
and

$$l + m + n = 8.$$